

KSR2010

PNP EPITAXIAL SILICON TRANSISTOR

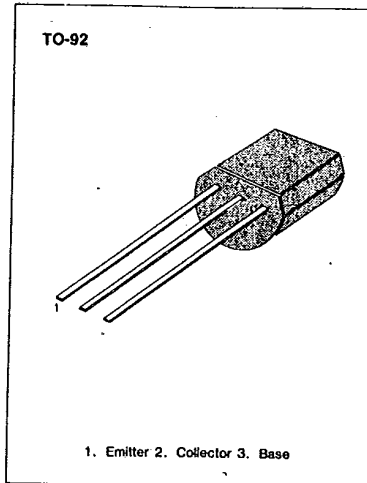
T-37-13

SWITCHING APPLICATION (Bias Resistor Built In)

- Switching Circuit, Inverter, Interface circuit
Driver circuit
- Built in bias Resistor (R=10K)
- Complement to KSR1010

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-40	V
Collector-Emitter Voltage	V _{CE0}	-40	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _c	-100	mA
Collector Dissipation	P _c	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ 150	°C

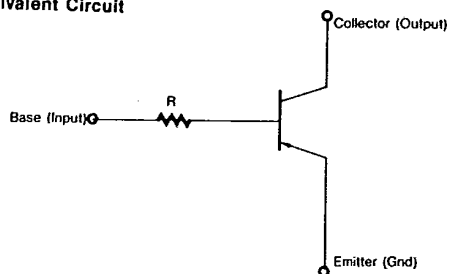


3

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV _{CB0}	I _c =-100μA, I _E =0	-40			V
Collector-Emitter Breakdown Voltage	BV _{CE0}	I _E =-1mA, I _B =0	-40			V
Collector Cutoff Current	I _{CB0}	V _{CB} =-30V, I _E =0			-0.1	μA
DC Current Gain	h _{FE}	V _{CE} =-5V, I _c =-1mA	100		600	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _c =-10mA, I _B =-1mA			0.3	V
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0 f=1MHz		5.5		pF
Current Gain-Bandwidth Product	f _T	V _{CE} =-10V, I _c =-5mA		200		MHz
Input Resistor	R		7	10	13	KΩ

Equivalent Circuit



KSR2010

PNP EPITAXIAL SILICON TRANSISTOR

T-37-13

